General Purpose Transistor

COMCHIP
SMD Diodes Specialist

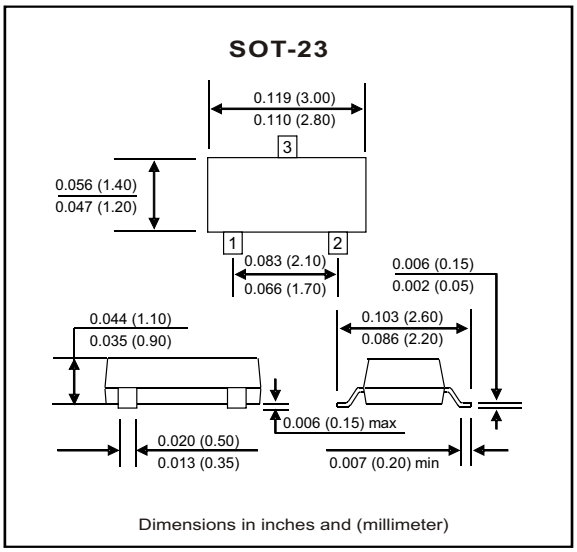
MMBT2907-G (PNP)

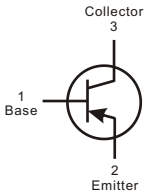
RoHS Device

Features

-Epitaxial planar die construction

-Device is designed as a general purpose amplifier and switching.





Maximum Ratings(at T_A=25°C unless otherwise noted)

Parameter	Symbol	Min	Max	Unit
Collector-Base voltage	V_{CBO}		-60	V
Powe r dissipatioin	P_{CM}		0.3	W
Collector current-Continuous	I_{CM}		-0.6	A
Storage tempe rature and junction tempe rature	T_{STG} , T_J	-55	+150	°C

Electrical Characteristics(at T_A=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Max	Unit
Collector-Base breakdown voltage	I_C=-10μA, I_E=0	$V_{(BR)CBO}$	-60		V
Collector-emitter breakdown voltage	I_C=-10mA, I_B=0	$V_{(BR)CEO}$	-40		V
Emitter-base breakdown voltage	I_E=-10μA, I_C=0	$V_{(BR)EBO}$	-5		V
Collector cut-off current	V_{CB}=-50V, I_E=0	I_{CBO}		-0.1	μA
Collector cut-off current	V_{CB}=-35V, I_B=0	I_{CEO}		-0.1	μA
Emitter cut-off current	V_{EB}=-3V, I_C=0	I_{EBO}		-0.1	μA
DC current gain	V_{CE}=-10V, I_C=-150mA	$h_{FE(1)}$	100	300	
	V_{CE}=-10V, I_C=-1mA	$h_{FE(2)}$	50		
Collector-emitter saturation voltage	I_C=-500mA, I_B=-50mA	$V_{CE(sat)}$		-1	V
Base-emitter saturation voltage	I_C=-500mA, I_B=-50mA	$V_{BE(sat)}$		-2	V
Transition frequency	V_{CE}=-20V, I_C=-50mA F=100MHz	f_T	200		Mhz